2764
64K (8K x 8) UV ERASABLE PROM

- **200 ns (2764-2) Maximum Access Time . . . HMOS*-E Technology**
- **Compatible with High-Speed 8mHz iAPX 186...Zero WAIT State**
- **Two Line Control**
- **Pin Compatible to 27128 EPROM**
- **Int$_e$ligent Programming™ Algorithm**
- **Industry Standard Pinout . . . JEDEC Approved**
- **Low Active Current...100mA Max.**
- **TTL Compatible**

The Intel 2764 is a 5V only, 65,536-bit ultraviolet erasable and electrically programmable read-only memory (EPROM). The standard 2764 access time is 250 ns with speed selection available at 200 ns. The access time is compatible with high-performance microprocessors such as Intel's 8 mHz iAPX 186. In these systems, the 2764 allows the microprocessor to operate without the addition of WAIT states. The 2764 is also compatible with the 12 MHz 8051 family.

An important 2764 feature is the separate output control, Output Enable ($\overline{OE}$) from the Chip Enable control ($\overline{CE}$). The $\overline{OE}$ control eliminates bus contention in microprocessor systems. Intel's Application Note AP-72 describes the microprocessor system implementation of the $\overline{OE}$ and $\overline{CE}$ controls on Intel's EPROMs. AP-72 is available from Intel's Literature Department.

The 2764 has a standby mode which reduces power consumption without increasing access time. The maximum active current is 100 mA, while the maximum standby current is only 40 mA. The standby mode is selected by applying a TTL-high signal to the $\overline{CE}$ input.

±10% V_{CC} tolerance is available as an alternative to the standard ±5% V_{CC} tolerance for the 2764. This can allow the system designer more leeway with regard to his power supply requirements and other system parameters.

The 2764 is fabricated with HMOS*-E technology, Intel's high-speed N-channel MOS Silicon Gate Technology.

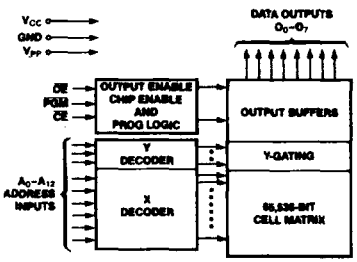
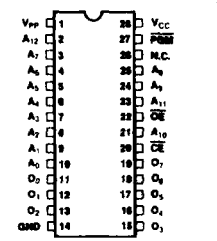


Figure 1. Block Diagram

27256	27128	2732A	2716
VPP	VPP		
A12	A12		
A7	A7	A7	A7
A6	A6	A6	A6
A5	A5	A5	A5
A4	A4	A4	A4
A3	A3	A3	A3
A2	A2	A2	A2
A1	A1	A1	A1
A0	A0	A0	A0
O0	O0	O0	O0
O1	O1	O1	O1
O2	O2	O2	O2
Gnd	Gnd	Gnd	Gnd

2764



2716	2732A	27128	27256
		VCC	VCC
		PGM	A14
VCC	VCC	A13	A13
A8	A8	A8	A8
A9	A9	A9	A9
VPP	A11	A11	A11
OE	OE/VPP	OE	OE
A10	A10	A10	A10
CE	CE	CE	CE
O7	O7	O7	O7
O6	O6	O6	O6
O5	O5	O5	O5
O4	O4	O4	O4
O3	O3	O3	O3

NOTE: INTEL "UNIVERSAL SITE"-COMPATIBLE EPROM PIN CONFIGURATIONS ARE SHOWN IN THE BLOCKS ADJACENT TO THE 2764 PINS

Figure 2. Pin Configurations

MODE SELECTION

MODE \ PINS	$\overline{CE}$ (20)	$\overline{OE}$ (22)	PGM (27)	A_9 (24)	V_{PP} (1)	V_{CC} (28)	Outputs (11-13, 15-19)
Read	V_{IL}	V_{IL}	V_{IH}	X	V_{CC}	V_{CC}	D_{OUT}
Output Disable	V_{IL}	V_{IH}	V_{IH}	X	V_{CC}	V_{CC}	High Z
Standby	V_{IH}	X	X	X	V_{CC}	V_{CC}	High Z
Program	V_{IL}	V_{IH}	V_{IL}	X	V_{PP}	V_{CC}	D_{IN}
Verify	V_{IL}	V_{IL}	V_{IH}	X	V_{PP}	V_{CC}	D_{OUT}
Program Inhibit	V_{IH}	X	X	X	V_{PP}	V_{CC}	High Z
int$_e$ligent Identifier	V_{IL}	V_{IL}	V_{IH}	V_H	V_{CC}	V_{CC}	Code
int$_e$ligent Programming	V_{IL}	V_{IH}	V_{IL}	X	V_{PP}	V_{CC}	D_{IN}

1. X can be V_{IH} or V_{IL}
2. V_H = 12.0V ± 0.5V

PIN NAMES

A_0-A_{12}	ADDRESSES
$\overline{CE}$	CHIP ENABLE
$\overline{OE}$	OUTPUT ENABLE
O_0-O_7	OUTPUTS
PGM	PROGRAM
N.C.	NO CONNECT

*HMOS is a patented process of Intel Corporation.

OCTOBER 1983
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ABSOLUTE MAXIMUM RATINGS*

Temperature Under Bias .....−10°C to +80°C
Storage Temperature .....−65°C to +125°C
All Input or Output Voltages with Respect to Ground ..... +7.0V to −0.6V
Voltage on Pin 28 with Respect to Ground .....+13.5V to −0.6V
V_{PP} Supply Voltage with Respect to Ground During Programming .....+22V to −0.6V

NOTICE: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

D.C. AND A.C. OPERATING CONDITIONS DURING READ

	2764-2	2764	2764-3	2764-4	2764-25	2764-30	2764-45
Operating Temperature Range	0°C–70°C	0°C–70°C	0°C–70°C	0°C–70°C	0°C–70°C	0°C–70°C	0°C–70°C
V_{CC} Power Supply[1,2]	5V ± 5%	5V ± 5%	5V ± 5%	5V ± 5%	5V ± 10%	5V ± 10%	5V ± 10%
V_{PP} Voltage[2]	$V_{PP} = V_{CC}$	$V_{PP} = V_{CC}$	$V_{PP} = V_{CC}$	$V_{PP} = V_{CC}$	$V_{PP} = V_{CC}$	$V_{PP} = V_{CC}$	$V_{PP} = V_{CC}$

READ OPERATION

D.C. CHARACTERISTICS

Symbol	Parameter	Limits				Conditions
		Min	Typ[3]	Max	Unit	
I_{LI}	Input Load Current			10	μA	$V_{IN} = 5.5V$
I_{LO}	Output Leakage Current			10	μA	$V_{OUT} = 5.5V$
I_{PP1}[2]	V_{PP} Current Read			5	mA	$V_{PP} = 5.5V$
I_{CC1}[2]	V_{CC} Current Standby			40	mA	$\overline{CE} = V_{IH}$
I_{CC2}[2]	V_{CC} Current Active		70	100	mA	$\overline{CE} = \overline{OE} = V_{IL}$
V_{IL}	Input Low Voltage	−.1		+.8	V	
V_{IH}	Input High Voltage	2.0		$V_{CC}+1$	V	
V_{OL}	Output Low Voltage			.45	V	$I_{OL} = 2.1$ mA
V_{OH}	Output High Voltage	2.4			V	$I_{OH} = -400$ μA

A.C. CHARACTERISTICS

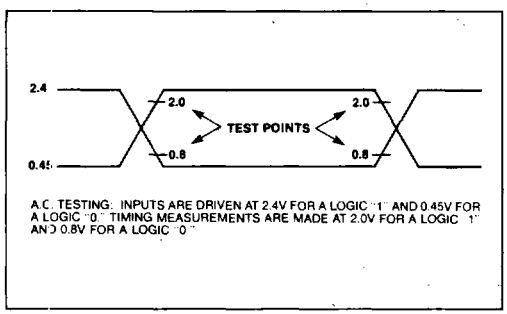
Symbol	Parameter	2764-2 Limits		2764-25 & 2764 Limits		2764-30 & 2764-3 Limits		2764-45 & 2764-4 Limits		Unit	Test Conditions
		Min	Max	Min	Max	Min	Max	Min	Max		
t_{ACC}	Address to Output Delay		200		250		300		450	ns	$\overline{CE} = \overline{OE} = V_{IL}$
t_{CE}	$\overline{CE}$ to Output Delay		200		250		300		450	ns	$\overline{OE} = V_{IL}$
t_{OE}	$\overline{OE}$ to Output Delay		75		100		120		150	ns	$\overline{CE} = V_{IL}$
t_{DF}[4]	$\overline{OE}$ High to Output Float	0	60	0	60	0	105	0	130	ns	$\overline{CE} = V_{IL}$
t_{OH}	Output Hold from Addresses, $\overline{CE}$ or $\overline{OE}$ Whichever Occurred First	0		0		0		0		ns	$\overline{CE} = \overline{OE} = V_{IL}$

NOTES: 1. V_{CC} must be applied simultaneously or before V_{PP} and removed simultaneously or after V_{PP}.
2. V_{PP} may be connected directly to V_{CC} except during programming. The supply current would then be the sum of I_{CC} and I_{PP1}.
3. Typical values are for $t_A = 25°C$ and nominal supply voltages.
4. This parameter is only sampled and is not 100% tested. Output Float is defined as the point where data is no longer driven — see timing diagram

CAPACITANCE ($T_A = 25°C$, f = 1MHz)

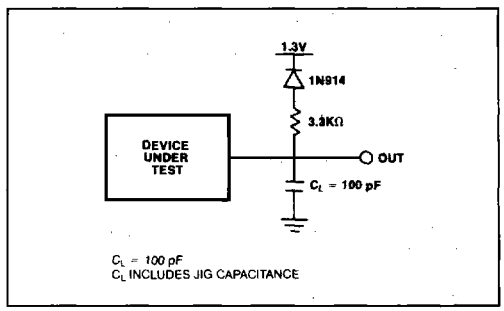
Symbol	Parameter	Typ.[1]	Max.	Unit	Conditions
C_{IN}[2]	Input Capacitance	4	6	pF	$V_{IN}=0V$
C_{OUT}	Output Capacitance	8	12	pF	$V_{OUT}=0V$

A.C. TESTING INPUT/OUTPUT WAVEFORM



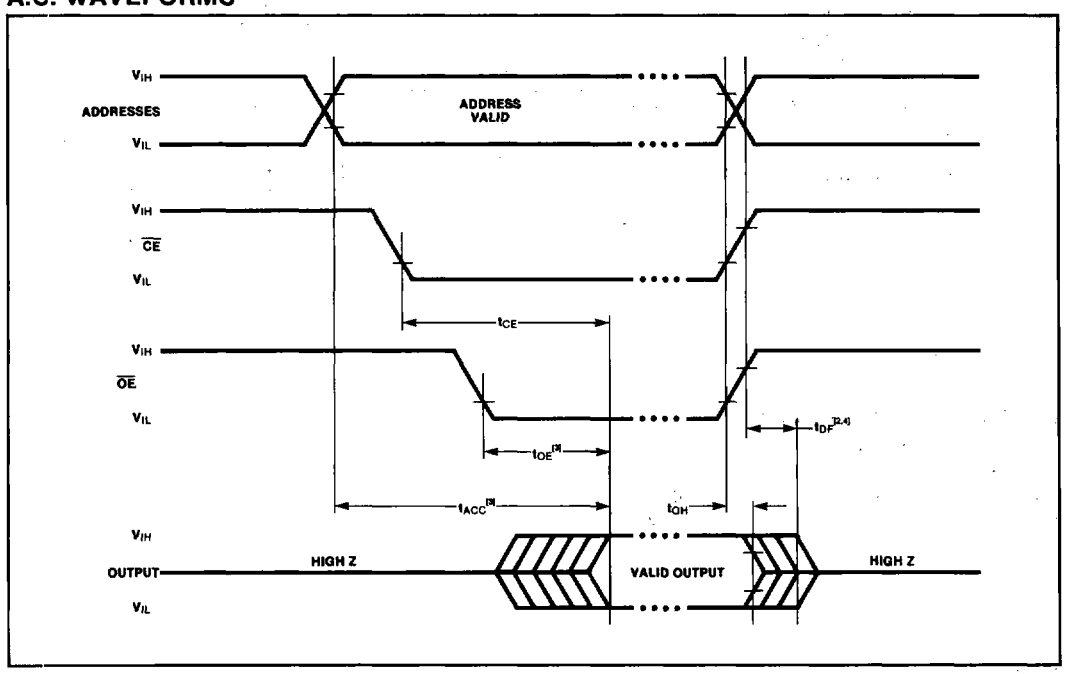
A.C. TESTING: INPUTS ARE DRIVEN AT 2.4V FOR A LOGIC "1" AND 0.45V FOR A LOGIC "0." TIMING MEASUREMENTS ARE MADE AT 2.0V FOR A LOGIC "1" AND 0.8V FOR A LOGIC "0."

A.C. TESTING LOAD CIRCUIT



C_L = 100 pF
C_L INCLUDES JIG CAPACITANCE

A.C. WAVEFORMS



NOTES: 1. *Typical values are for T_A = 25°C and nominal supply voltages.*
2. This parameter is only sampled and is not 100% tested.
3. $\overline{OE}$ may be delayed up to $t_{ACC} - t_{OE}$ after the falling edge of $\overline{CE}$ without impact on t_{ACC}.
4. t_{DF} is specified from $\overline{OE}$ or $\overline{CE}$, whichever occurs first. Output float is defined as the point where data is no longer driven.

STANDARD PROGRAMMING

D.C. PROGRAMMING CHARACTERISTICS: $T_A = 25 \pm 5°C$, $V_{CC} = 5V \pm 5\%$, $V_{PP} = 21V \pm 0.5V$ (see Note 1)

Symbol	Parameter	Limits			Test Conditions
		Min.	Max.	Unit	
I_{LI}	Input Current (All Inputs)		10	μA	$V_{IN} = V_{IL}$ or V_{IH}
V_{IL}	Input Low Level (All Inputs)	−0.1	0.8	V	
V_{IH}	Input Hight Level	2.0	$V_{CC}+1$	V	
V_{OL}	Output Low Voltage During Verify		0.45	V	$I_{OL} = 2.1$ mA
V_{OH}	Output High Voltage During Verify	2.4		V	$I_{OH} = -400$ μA
I_{CC2}	V_{CC} Supply Current (Program & Verify)		100	mA	
I_{PP2}	V_{PP} Supply Current (Program)		30	mA	$\overline{CE} = V_{IL} = \overline{PGM}$
V_{ID}	Ag for int$_e$ligent Identifier Voltage	11.5	12.5	V	

A.C. PROGRAMMING CHARACTERISTICS: $T_A = 25 \pm 5°C$, $V_{CC} = 5V \pm 5\%$, $V_{PP} = 21V \pm 0.5V$ (see Note 1)

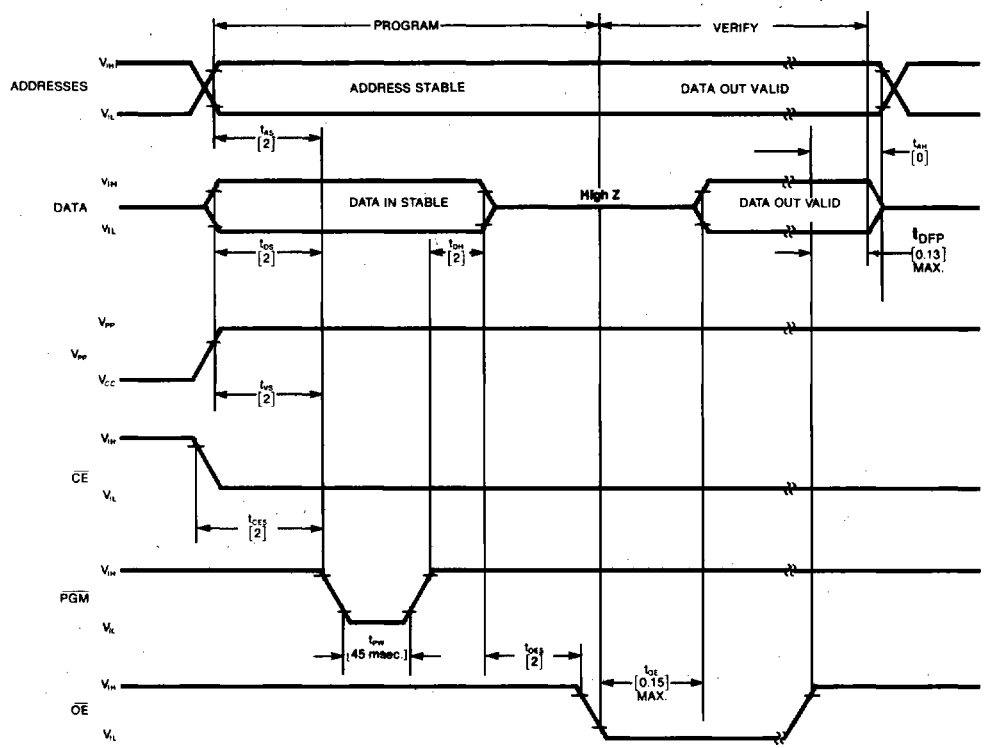
Symbol	Parameter	Limits				Test Conditions*
		Min.	Typ.	Max.	Unit	
t_{AS}	Address Setup Time	2			μs	
t_{OES}	$\overline{OE}$ Setup Time	2			μs	
t_{DS}	Data Setup Time	2			μs	
t_{AH}	Address Hold Time	0			μs	
t_{DH}	Data Hold Time	2			μs	
t_{DFP}[2]	Output Enable to Output Float Delay	0		130	ns	
t_{VS}	V_{PP} Setup Time	2			μs	
t_{PW}	$\overline{PGM}$ Pulse Width During Programming	45	50	55	ms	
t_{CES}	$\overline{CE}$ Setup Time	2			μs	
t_{OE}	Data Valid from $\overline{OE}$			150	ns	

*A.C. CONDITIONS OF TEST

Input Rise and Fall Times (10% to 90%) 20ns
Input Pulse Levels ..... 0.45V to 2.4V
Input Timing Reference Level ..... 0.8V and 2.0V
Output Timing Reference Level ..... 0.8V and 2.0V

NOTES:
1. V_{CC} *must be applied simultaneously or before* V_{PP} *and removed simultaneously or after* V_{PP}.
2. This parameter is only sampled and is not 100% tested. Output Float is defined as the point where data is no longer driven — see timing diagram

STANDARD PROGRAMMING WAVEFORMS



1. ALL TIMES SHOWN IN [ ] ARE MINIMUM AND IN μSEC UNLESS OTHERWISE SPECIFIED.
2. THE INPUT TIMING REFERENCE LEVEL IS .8V FOR V_{IL} AND 2V FOR A V_{IH}.
3. t_{OE} AND t_{DFP} ARE CHARACTERISTICS OF THE DEVICE BUT MUST BE ACCOMMODATED BY THE PROGRAMMER.
4. WHEN PROGRAMMING THE 2764, A 0.1μF CAPACITOR IS REQUIRED ACROSS V_{PP} AND GROUND TO SUPRESS SPURIOUS VOLTAGE TRANSIENTS WHICH CAN DAMAGE THE DEVICE.

ERASURE CHARACTERISTICS

The erasure characteristics of the 2764 are such that erasure begins to occur upon exposure to light with wavelengths shorter than approximately 4000 Angstroms (A). It should be noted that sunlight and certain types of fluorescent lamps have wavelengths in the 3000–4000 Å range. Data show that constant exposure to room level fluorescent lighting could erase the typical 2764 in approximately 3 years, while it would take approximately 1 week to cause erasure when exposed to direct sunlight. If the 2764 is to be exposed to these types of lighting conditions for extended periods of time, opaque labels should be placed over the 2764 window to prevent unintentional erasure.

The recommended erasure procedure for the 2764 is exposure to shortwave ultraviolet light which has a wavelength of 2537 Angstroms (Å). The integrated dose (i.e., UV intensity × exposure time) for erasure should be a minimum of 15 W-sec/cm^2. The erasure time with this dosage is approximately 15 to 20 minutes using an ultraviolet lamp with a 12000 μW/cm^2 power rating. The 2764 should be placed within 1 inch of the lamp tubes during erasure. The maximum integrated dose a 2764 can be exposed to without damage is 7258 Wsec/cm^2 (1 week @ 12000 μW/cm^2). Exposure of the 2764 to high intensity UV light for long periods may cause permanent damage.

DEVICE OPERATION

The eight modes of operation of the 2764 are listed in Table 1. A single 5V power supply is required in the read mode. All inputs are TTL levels except for V_{PP} and 12V on A9 for int$_e$ligent Identifier mode.

Table 1. MODE SELECTION

MODE \ PINS	$\overline{CE}$ (20)	$\overline{OE}$ (22)	$\overline{PGM}$ (27)	A_9 (24)	V_{PP} (1)	V_{CC} (28)	Outputs (11-13, 15-19)
Read	V_{IL}	V_{IL}	V_{IH}	X	V_{CC}	V_{CC}	D_{OUT}
Output Disable	V_{IL}	V_{IH}	V_{IH}	X	V_{CC}	V_{CC}	High Z
Standby	V_{IH}	X	X	X	V_{CC}	V_{CC}	High Z
Program	V_{IL}	V_{IH}	V_{IL}	X	V_{PP}	V_{CC}	D_{IN}
Verify	V_{IL}	V_{IL}	V_{IH}	X	V_{PP}	V_{CC}	D_{OUT}
Program Inhibit	V_{IH}	X	X	X	V_{PP}	V_{CC}	High Z
intelligent Identifier	V_{IL}	V_{IL}	V_{IH}	V_H	V_{CC}	V_{CC}	Code
intelligent Programming	V_{IL}	V_{IH}	V_{IL}	X	V_{PP}	V_{CC}	D_{IN}

NOTES:
1. X can be V_{IH} or V_{IL}
2. $V_H = 12.0V \pm 0.5V$

READ MODE

The 2764 has two control functions, both of which must be logically active in order to obtain data at the outputs. Chip Enable ($\overline{CE}$) is the power control and should be used for device selection. Output Enable ($\overline{OE}$) is the output control and should be used to gate data from the output pins, independent of device selection. Assuming that addresses are stable, the address access time (t_{ACC}) is equal to the delay from $\overline{CE}$ to output (t_{CE}). Data is available at the outputs after a delay of t_{OE} from the falling edge of $\overline{OE}$, assuming that $\overline{CE}$ has been low and addresses have been stable for at least $t_{ACC} - t_{OE}$.

STANDBY MODE

The 2764 has standby mode which reduces the maximum active current from 100 mA to 40 mA. The 2764 is placed in the standby mode by applying a TTL-high signal to the $\overline{CE}$ input. When in standby mode, the outputs are in a high impedance state, independent of the $\overline{OE}$ input.

Output OR-Tieing

Because EPROMs are usually used in larger memory arrays. Intel has provided 2 control lines which accommodate this multiple memory connection. The two control lines allow for:

a) the lowest possible memory power dissipation, and
b) complete assurance that output bus contention will not occur.

To use these two control lines most efficiently. $\overline{CE}$ (pin 20) should be decoded and used as the primary device selecting function, while $\overline{OE}$ (pin 22) should be made a common connection to all devices in the array and connected to the $\overline{READ}$ line from the system control bus. This assures that all deselected memory devices are in their low power standby mode and that the output pins are active only when data is desired from a particular memory device.

System Considerations

The power switching characteristics of HMOS-E EPROMs require careful decoupling of the devices. The supply current, I_{CC}, has three segments that are of interest to the system designer — the standby current level, the active current level, and the transient current peaks that are produced by the falling and rising edges of Chip Enable. The magnitude of these transient current peaks is dependent on the output capacitance loading of the device. The associated transient voltage peaks can be suppressed by complying with Intel's Two-Line Control, as detailed in Intel's Application Note, AP-72, and by properly selected decoupling capacitors. It is recommended that a 0.1 μF ceramic capacitor be used on every device between V_{CC} and GND. This should be a high frequency capacitor of low inherent inductance and should be placed as close to the device as possible. In addition, a 4.7 μF bulk electrolytic capacitor should be used between V_{CC} and GND for every eight devices. The bulk capacitor should be located near where the power supply is connected to the array. The purpose of the bulk capacitor is to overcome the voltage droop caused by the inductive effect of PC board-traces.

PROGRAMMING MODES

Caution: Exceeding 22V on pin 1 (V_{PP}) will permanently damage the 2764.

"1" state. Data is introduced by selectively programming "0s" into the desired bit locations. Although only "0s" will be programmed, both "1s" and "0s" can be present in the data word. The only way to change a "0" to a "1" is by ultraviolet light erasure.

The 2764 is in the programming mode when V_{PP} input is at 21V and $\overline{CE}$ and $\overline{PGM}$ are both at TTL low. The data to be programmed is applied 8 bits in parallel to the data output pins. The levels required for the address and data inputs are TTL.

Standard Programming

For programming, $\overline{CE}$ should be kept TTL-low at all times while V_{PP} is kept at 21V. When the address and data are stable, a 50 msec, active-low, TTL program pulse is applied to the $\overline{PGM}$ input. A program pulse must be applied at each address location to be programmed. You can program any location at any time—either individually, sequentially, or at random. The program pulse has a maximum width of 55 msec.

Programming of multiple 2764s in parallel with the same data can be easily accomplished due to the simplicity of the programming requirements. Like inputs of the paralleled 2764s may be connected together when they are programmed with the same data. A low-level TTL pulse applied to the $\overline{PGM}$ input programs the paralleled 2764s.

Program Inhibit

Programming of multiple 2764s in parallel with different data is also easily accomplished by using the Program inhibit

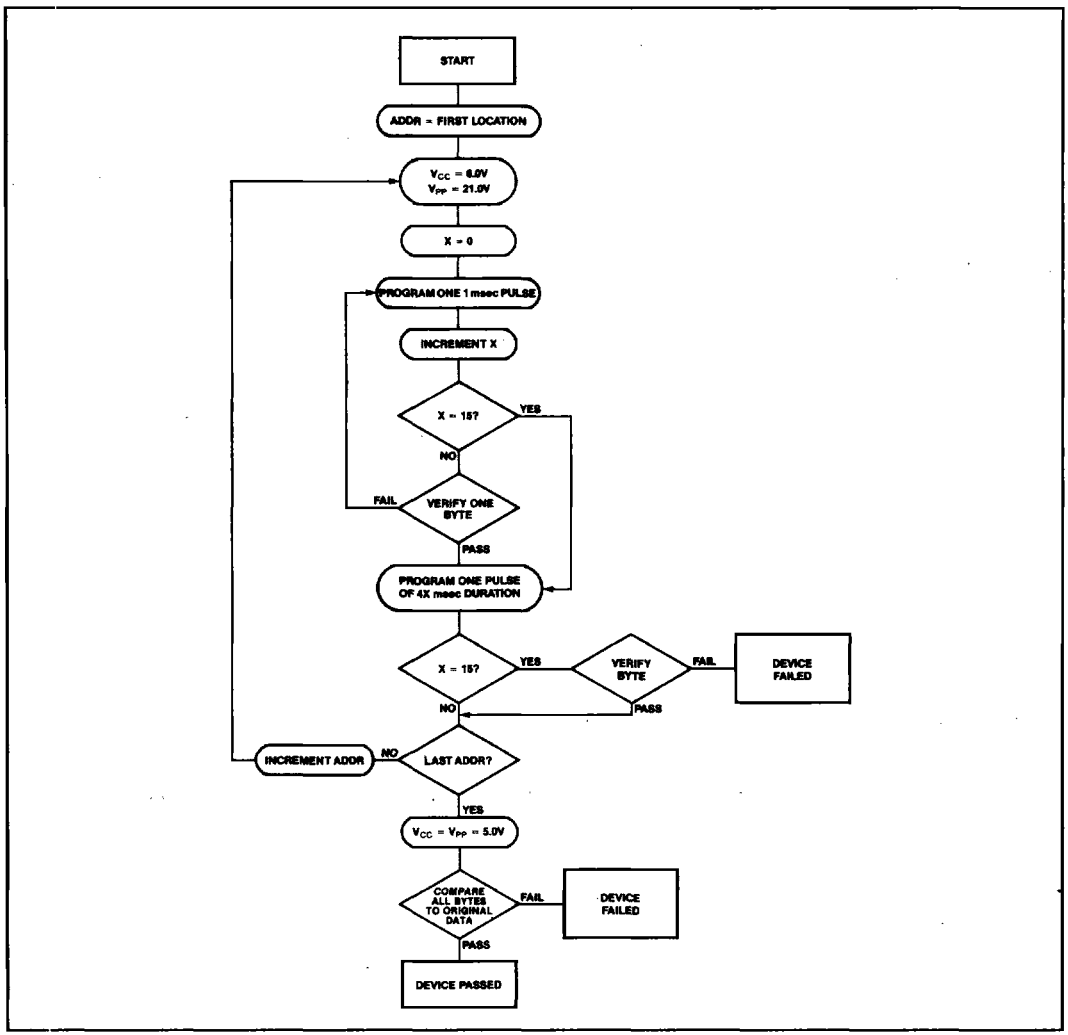


Figure 3. 2764 int$_e$ligent Programming™ Flowchart

mode. A high-level $\overline{CE}$ or $\overline{PGM}$ input inhibits the other 2764s from being programmed. Except for $\overline{CE}$, all like inputs (including $\overline{OE}$) of the parallel 2764s may be common. A TTL low-level pulse applied to a 2764 $\overline{CE}$ and $\overline{PGM}$ input with V_{PP} at 21V will program that 2764.

Verify

A verify should be performed on the programmed bits to determine that they were correctly programmed. The verify is performed with $\overline{CE}$ and $\overline{OE}$ at V_{IL}, $\overline{PGM}$ at V_{IH} and V_{PP} at 21V.

int$_e$ligent Programming™ Algorithm

The 2764 int$_e$ligent Programming Algorithm is the preferred programming method since it allows Intel 2764s to be programmed in a significantly faster time than the standard 50 msec per-byte programming routine. Typical programming times for 2764s are on the order of a minute and a half, which is a five-fold reduction in programming time from the standard method. This fast algorithm results in improved reliability characteristics compared to the standard 50 msec algorithm. A flowchart of the int$_e$ligent Programming Algorithm is shown in Figure 3. This is compatible with the 27128 int$_e$ligent Programming Algorithm.

This fast algorithm results in high reliability characteristics through the "closed loop" technique of margin checking. To ensure reliable program margin the int$_e$ligent Programming Algorithm utilizes two different pulse types: initial and over-program. The duration of the initial $\overline{PGM}$ pulse(s) is one millisecond, which will then be followed by a longer over-program pulse of length 4X msec. X is an iteration counter and is equal to the number of the initial one millisecond pulses applied to a particular 2764 location, before a correct verify occurs. Up to 15 one-millisecond pulses per byte are provided for before the overprogram pulse is applied.

The entire sequence of program pulses and byte verifications is performed at V_{CC} = 6.0V and V_{PP} = 21.0V. When the int$_e$ligent Programming cycle has been completed, all bytes should be compared to the original data with $V_{CC} = V_{PP} = 5.0V$.

int$_e$ligent Programming™ Algorithm

D.C. PROGRAMMING CHARACTERISTICS: $T_A = 25 \pm 5°C$, $V_{CC} = 6.0V \pm 0.25V$, $V_{PP} = 21V \pm 0.5V$ (see Note 1)

Symbol	Parameter	Limits			Test Conditions
		Min.	Max.	Unit	
I_{LI}	Input Current (All Inputs)		10	μA	$V_{IN} = V_{IL}$ or V_{IH}
V_{IL}	Input Low Level (All Inputs)	−0.1	0.8	V	
V_{IH}	Input High Level	2.0	V_{CC}	V	
V_{OL}	Output Low Voltage During Verify		0.45	V	I_{OL} = 2.1 mA
V_{OH}	Output High Voltage During Verify	2.4		V	I_{OH} = −400 μA
I_{CC2}	V_{CC} Supply Current (Program & Verify)		100	mA	
I_{PP2}	V_{PP} Supply Current (Program)		30	mA	$\overline{CE} = V_{IL} = \overline{PGM}$
V_{ID}	Ag for int$_e$ligent Identifier Voltage	11.5	12.5	V	

A.C. PROGRAMMING CHARACTERISTICS: $T_A = 25 \pm 5°C$, $V_{CC} = 6.0V \pm 0.25V$, $V_{PP} = 21V \pm 0.5V$ (see Note 1)

Symbol	Parameter	Limits				Test Conditions*
		Min.	Typ.	Max.	Unit	
t_{AS}	Address Setup Time	2			μs	
t_{OES}	$\overline{OE}$ Setup Time	2			μs	
t_{DS}	Data Setup Time	2			μs	
t_{AH}	Address Hold Time	0			μs	
t_{DH}	Data Hold Time	2			μs	(see Note 4)
t_{DFP}	$\overline{OE}$ High to Output Float Delay	0		130	ns	
t_{VPS}	V_{PP} Setup Time	2			μs	
t_{VCS}	V_{CC} Setup Time	2			μs	
t_{PW}	$\overline{PGM}$ Initial Program Pulse Width	0.95	1.0	1.05	ms	(see Note 3)
t_{OPW}	$\overline{PGM}$ Overprogram Pulse Width	3.8		63	ms	(see Note 2)
t_{CES}	$\overline{CE}$ Setup Time	2			μs	
t_{OE}	Data Valid from $\overline{OE}$			150	ns	

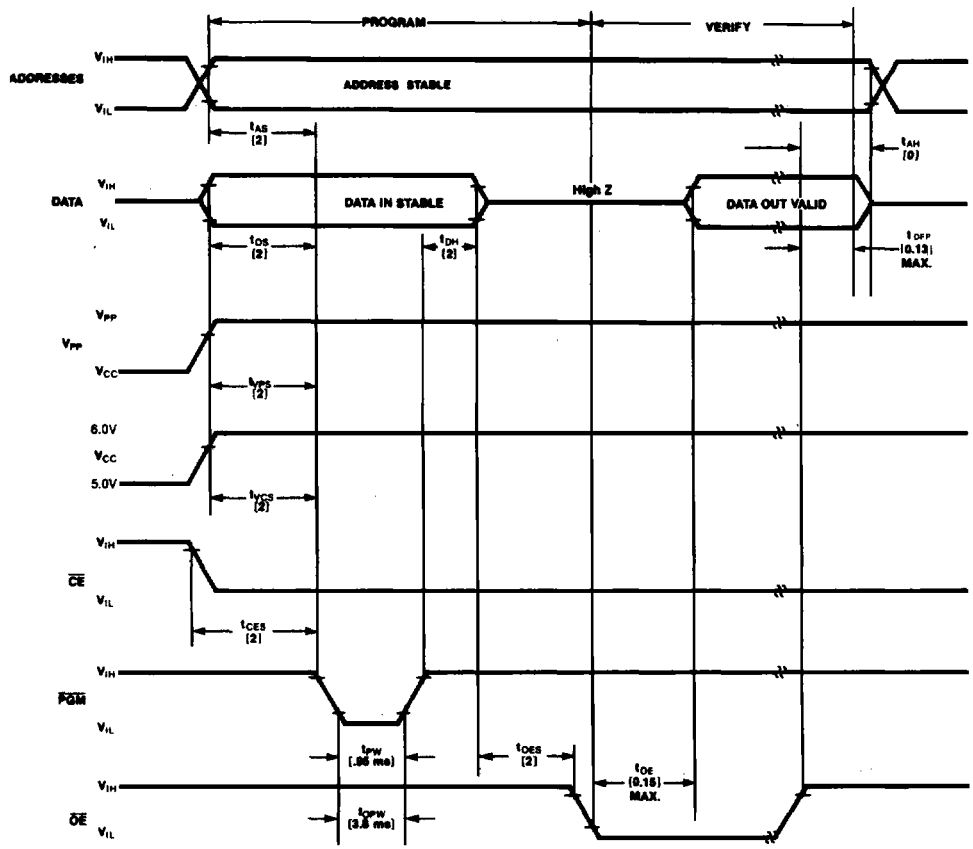
***A.C. CONDITIONS OF TEST**

Input Rise and Fall Times (10% to 90%) ..... 20 ns
Input Pulse Levels ..... 0.45V to 2.4V
Input Timing Reference Level ..... 0.8V and 2.0V
Output Timing Reference Level ..... 0.8V and 2.0V

NOTES:

1. V_{CC} must be applied simultaneously or before V_{PP} and removed simultaneously or after V_{PP}.
2. The length of the overprogram pulse will vary from 3.8 msec to 63 msec as a function of the iteration counter value X.
3. Initial Program Pulse width tolerance is 1 msec ± 5%.
4. This parameter is only sampled and is not 100% tested. Output Float is defined as the point where data is no longer driven — see timing diagram

intelligent Programming™ WAVEFORMS



1. ALL TIMES SHOWN IN [ ] ARE MINIMUM AND IN μSEC UNLESS OTHERWISE SPECIFIED.
2. THE INPUT TIMING REFERENCE LEVEL IS .8V FOR V_{IL} AND 2V FOR A V_{IH}.
3. t_{OE} AND t_{DFP} ARE CHARACTERISTICS OF THE DEVICE BUT MUST BE ACCOMMODATED BY THE PROGRAMMER.
4. WHEN PROGRAMMING THE R2784 A 0.1μF CAPACITOR IS REQUIRED ACROSS V_{PP} AND GROUND TO SUPRESS SPURIOUS VOLTAGE TRANSIENTS WHICH CAN DAMAGE THE DEVICE.

int$_e$ligent Identifier™ Mode

The int$_e$ligent Identifier Mode allows the reading out of a binary code from an EPROM that will identify its manufacturer and type. This mode is intended for use by programming equipment for the purpose of automatically matching the device to be programmed with its corresponding programming algorithm. This mode is functional in the 25°C ± 5°C ambient temperature range.

To activate this mode, the programming equipment must force 11.5V to 12.5V on address line A9 (pin 24) of the 2764. Two identifier bytes may then be sequenced from the device outputs by toggling address line A0 (pin 10) from V_{IL} to V_{IH}. All other address lines must be held at V_{IL} during int$_e$ligent Identifier Mode.

Byte 0 (A0 = V_{IL}) represents the manufacturer code and byte 1 (A0 = V_{IH}) the device identifier code. For the Intel 2764, these two identifier bytes are given in Table 2. All identifiers for manufacturer and device codes will possess odd parity, with the MSB (O_7) defined as the parity bit.

During 1982, Intel will begin manufacturing 2764s that will contain the int$_e$ligent Identifier feature. Earlier generation devices will not contain identifier information, and if erased, will respond with a "one" (V_{OH}) on each data line when operated in this mode. Programmed, pre-identifier mode 2764s will respond with the current data contained in locations 0 to 1 when subjected to the int$_e$ligent Identifier operation.

Table 2. 2764 int$_e$ligent Identifier™ Bytes

Pins / Identifier	A_0 (10)	O_7 (19)	O_6 (18)	O_5 (17)	O_4 (16)	O_3 (15)	O_2 (13)	O_1 (12)	O_0 (11)	Hex Data
Manufacturer Code	V_{IL}	1	0	0	0	1	0	0	1	89
Device Code	V_{IH}	0	0	0	0	0	0	1	0	02